

| Part | Remarks |
|--------------|--|
| SFH6751-X009 | 5 kV/μs, Dual channel, SMD-8 (option 9) |
| SFH6752 | 10 kV/μs, Dual channel, DIP-8 |
| SFH6752-X006 | 10 kV/μs, Dual channel, DIP-8 400 mil (option 6) |
| SFH6752-X007 | 10 kV/μs, Dual channel, SMD-8 (option 7) |
| SFH6752-X009 | 10 kV/μs, Dual channel, SMD-8 (option 9) |

Truth Table (Positive Logic)

| LED | ENABLE | OUTPUT |
|-----|--------|--------|
| ON | H | L |
| OFF | H | H |
| ON | L | H |
| OFF | L | H |
| ON | NC | L |
| OFF | NC | H |

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

| Parameter | Test condition | Symbol | Value | Unit |
|---------------------------------------|------------------------------|-----------|-------------------------|------|
| Average forward current ¹⁾ | | I_F | 20 | mA |
| Average forward current ²⁾ | | I_F | 15 | mA |
| Reverse input voltage | | V_R | 5 | V |
| Enable input voltage ¹⁾ | | V_E | $V_{CC} + 0.5\text{ V}$ | V |
| Enable input current ¹⁾ | | I_E | 5 | mA |
| Surge current | $t = 100\text{ }\mu\text{s}$ | I_{FSM} | 200 | mA |

¹⁾ Package: Single DIP-8

²⁾ Package: Dual DIP-8

Output

| Parameter | Test condition | Symbol | Value | Unit |
|--|----------------|------------|-------|------|
| Supply voltage | 1 minute max. | V_{CC} | 7 | V |
| Output current | | I_O | 50 | mA |
| Output voltage | | V_O | 7 | V |
| Output power dissipation ¹⁾ | | P_{diss} | 85 | mW |
| Output power dissipation per channel ²⁾ | | P_{diss} | 60 | mW |

¹⁾ Package: Single DIP-8

²⁾ Package: Dual DIP-8

Coupler

| Parameter | Test condition | Symbol | Value | Unit |
|---|-----------------------|-----------|---------------|--------------------|
| Storage temperature | | T_{stg} | - 55 to + 150 | $^{\circ}\text{C}$ |
| Operating temperature | | T_{amb} | - 40 to + 100 | $^{\circ}\text{C}$ |
| Lead solder temperature ¹⁾ | for 10 sec. | | 260 | $^{\circ}\text{C}$ |
| Solder reflow temperature ²⁾ | for 1 minute | | 260 | $^{\circ}\text{C}$ |
| Isolation test voltage | $t = 1.0\text{ sec.}$ | V_{ISO} | 5300 | V_{RMS} |

¹⁾ Package: DIP-8 through hole

²⁾ Package: DIP-8 SMD



Recommended Operating Conditions

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|---------------------------|--------------------------|-----------|------|------|----------|------|
| Operating temperature | | T_{amb} | - 40 | | 100 | °C |
| Supply voltage | | V_{cc} | 4.5 | | 5.5 | V |
| Input current low level | | I_{FL} | 0 | | 250 | μA |
| Input current high level | | I_{FH} | 5 | | 15 | mA |
| Logic high enable voltage | | V_{EH} | 2.0 | | V_{CC} | V |
| Logic low enable voltage | | V_{EL} | 0.0 | | 0.8 | V |
| Output pull up resistor | | R_L | 330 | | 4 K | Ω |
| Fanout | $R_L = 1\text{ k}\Omega$ | N | | | 5 | - |

Electrical Characteristics

$T_{amb} = 25\text{ °C}$ and $V_{cc} = 5.5\text{ V}$, unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-----------------------|---|--------|-----|------|-----|------|
| Input forward voltage | $I_F = 10\text{ mA}$ | V_F | 1.1 | 1.4 | 1.7 | V |
| Reverse current | $V_R = 4.5\text{ V}$ | I_R | | 1 | | μA |
| Input capacitance | $f = 1\text{ MHz}$, $V_F = 0\text{ V}$ | C_I | | 55 | | pF |

Output

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--|--|-----------|-----|-------|-------|------|
| High level supply current (single channel) | $V_E = 0.5\text{ V}$, $I_F = 0\text{ mA}$ | I_{CCH} | | 4.1 | 7.0 | mA |
| | $V_E = V_{CC}$, $I_F = 0\text{ mA}$ | I_{CCH} | | 3.3 | 6.0 | mA |
| High level supply current (dual channel) | $I_F = 0\text{ mA}$ | I_{CCH} | | 8.2 | 14.0 | mA |
| Low level supply current | $V_E = 0.5\text{ V}$, $I_F = 10\text{ mA}$ | I_{CCL} | | 4.0 | 7.0 | mA |
| | $V_E = V_{CC}$, $I_F = 10\text{ mA}$ | I_{CCL} | | 3.3 | 6.0 | mA |
| High level output current | $V_E = 2.0\text{ V}$, $V_O = 5.5\text{ V}$, $I_F = 250\text{ }\mu\text{A}$ | I_{OH} | | 0.002 | 1 | μA |
| Low level output voltage | $V_E = 2.0\text{ V}$, $I_F = 5\text{ mA}$, $I_{OL}(\text{sinking}) = 13\text{ mA}$ | V_{OL} | | 0.2 | 0.6 | V |
| Input threshold current | $V_E = 2.0\text{ V}$, $V_O = 5.5\text{ V}$, $I_{OL}(\text{sinking}) = 13\text{ mA}$ | I_{TH} | | 2.4 | 5.0 | mA |
| High level enable current | $V_E = 2.0\text{ V}$ | I_{EH} | | - 0.6 | - 1.6 | mA |
| Low level enable current | $V_E = 0.5\text{ V}$ | I_{EL} | | - 0.8 | - 1.6 | mA |
| High level enable voltage | | V_{EH} | 2.0 | | | V |
| Low level enable voltage | | V_{EL} | | | 0.8 | V |

Switching Characteristics

Over Recommended Temperature ($T_a = -40$ to $+100$ °C), $V_{CC} = 5$ V, $I_F = 7.5$ mA unless otherwise specified.
 All Typical at $T_a = 25$ °C, $V_{CC} = 5$ V.

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--|---|-----------------------|-----|------|-----|------|
| Propagation delay time to high output level | $R_L = 350 \Omega$, $C_L = 15$ pF | t_{PLH} | 20 | 48 | 75* | ns |
| | | t_{PLH} | | | 100 | ns |
| Propagation delay time to low output level | $R_L = 350 \Omega$, $C_L = 15$ pF | t_{PHL} | 25 | 50 | 75* | ns |
| | | t_{PHL} | | | 100 | ns |
| Pulse width distortion | $R_L = 350 \Omega$, $C_L = 15$ pF | $ t_{PHL} - t_{PLH} $ | | 2.9 | 35 | ns |
| Propagation delay skew | $R_L = 350 \Omega$, $C_L = 15$ pF | t_{PSK} | | 8 | 40 | ns |
| Output rise time (10 - 90 %) | $R_L = 350 \Omega$, $C_L = 15$ pF | t_r | | 23 | | ns |
| Output fall time (90 - 10 %) | $R_L = 350 \Omega$, $C_L = 15$ pF | t_f | | 7 | | ns |
| Propagation delay time of enable from V_{EH} to V_{EL} | $R_L = 350 \Omega$, $C_L = 15$ pF, $V_{EL} = 0$ V, $V_{EH} = 3$ V | t_{ELH} | | 12 | | ns |
| Propagation delay time of enable from V_{EL} to V_{EH} | $R_L = 350 \Omega$, $C_L = 15$ pF, $V_{EL} = 0$ V, $V_{EH} = 3$ V | t_{EHL} | | 11 | | ns |

* 75ns applies to the 6N137 only, a JEDEC registered specification

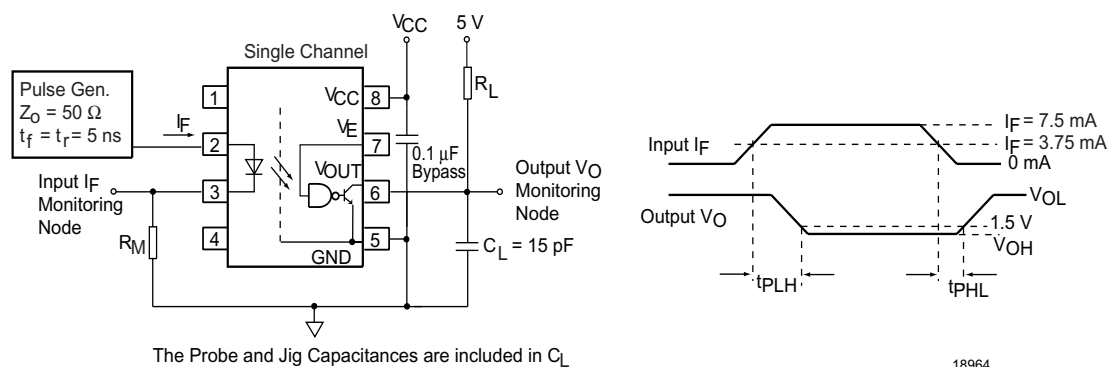


Figure 1. Single Channel Test Circuit for t_{PLH} , t_{PHL} , t_r and t_f

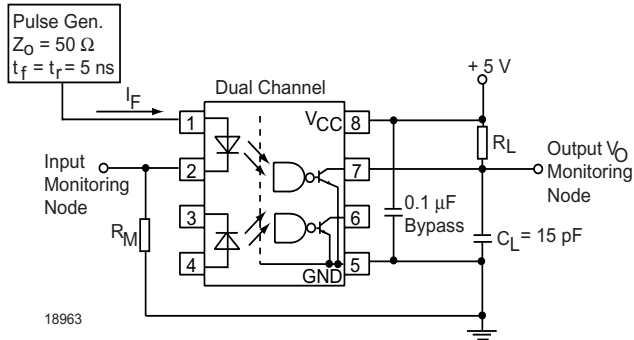
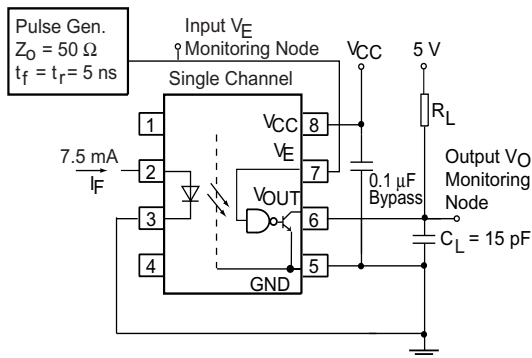
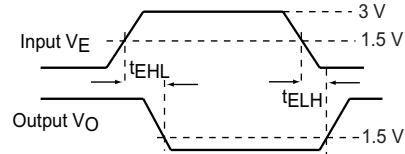


Figure 2. Dual Channel Test Circuit for t_{PLH} , t_{PHL} , t_r and t_f



The Probe and Jig Capacitances are included in C_L



18975

Figure 3. Single Channel Test Circuit for t_{EHL} and t_{ELH}

Common Mode Transient Immunity

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|---------------------------------------|--|----------|-------|-------|-----|------------------|
| Common mode transient immunity (high) | $ V_{CM} = 10\text{ V}$, $V_{CC} = 5\text{ V}$, $I_F = 0\text{ mA}$, $V_{O(\min)} = 2\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^1$ | $ CM_H $ | 100 | | | V/ μs |
| | $ V_{CM} = 50\text{ V}$, $V_{CC} = 5\text{ V}$, $I_F = 0\text{ mA}$, $V_{O(\min)} = 2\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^2$ | $ CM_H $ | 5000 | 10000 | | V/ μs |
| | $ V_{CM} = 1\text{ kV}$, $V_{CC} = 5\text{ V}$, $I_F = 0\text{ mA}$, $V_{O(\min)} = 2\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^3$ | $ CM_H $ | 10000 | 15000 | | V/ μs |
| | $ V_{CM} = 10\text{ V}$, $V_{CC} = 5\text{ V}$, $I_F = 7.5\text{ mA}$, $V_{O(\min)} = 0.8\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^1$ | $ CM_L $ | 100 | | | V/ μs |
| | $ V_{CM} = 50\text{ V}$, $V_{CC} = 5\text{ V}$, $I_F = 7.5\text{ mA}$, $V_{O(\min)} = 0.8\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^2$ | $ CM_L $ | 5000 | 10000 | | V/ μs |
| | $ V_{CM} = 1\text{ kV}$, $V_{CC} = 5\text{ V}$, $I_F = 7.5\text{ mA}$, $V_{O(\min)} = 0.8\text{ V}$, $R_L = 350\ \Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}^3$ | $ CM_L $ | 10000 | 15000 | | V/ μs |

1) For 6N137 and SFH6750

2) For SFH6741 and SFH6751

3) For SFH6742 and SFH6752

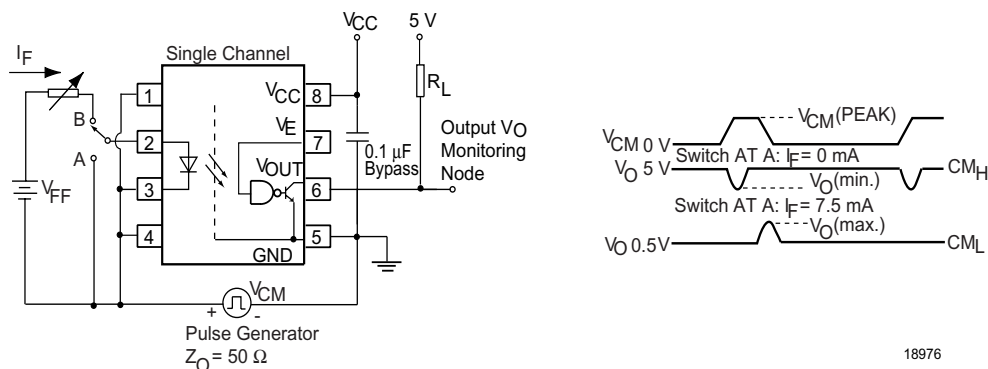


Figure 4. Single Channel Test Circuit for Common Mode Transient Immunity

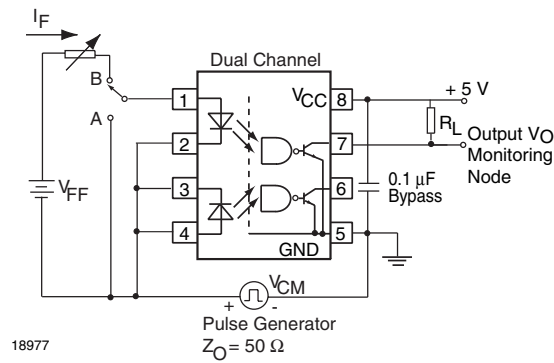


Figure 5. Dual Channel Test Circuit for Common Mode Transient Immunity

Safety and Insulation Ratings

As per IEC60747-5-2, §7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--|----------------|--------|------|-----------|-----|------|
| Climatic Classification (according to IEC 68 part 1) | | | | 55/110/21 | | |
| Comparative Tracking Index | | CTI | 175 | | 399 | |
| V_{IOTM} | | | 8000 | | | V |
| V_{IORM} | | | 630 | | | V |
| P_{SI} | | | | | 500 | mW |
| I_{SI} | | | | | 300 | mA |
| T_{SI} | | | | | 175 | °C |
| Creepage | standard DIP-8 | | 7 | | | mm |
| Clearance | standard DIP-8 | | 7 | | | mm |
| Creepage | 400mil DIP-8 | | 8 | | | mm |
| Clearance | 400mil DIP-8 | | 8 | | | mm |
| Insulation thickness | | | 0.2 | | | mm |

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

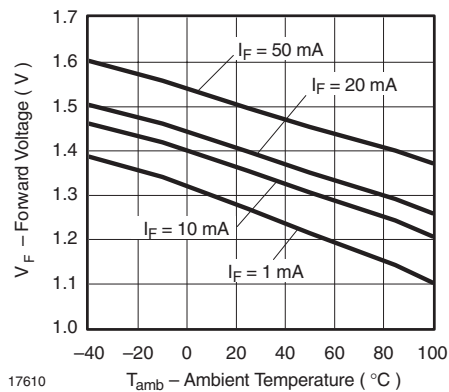


Figure 6. Forward Voltage vs. Ambient Temperature

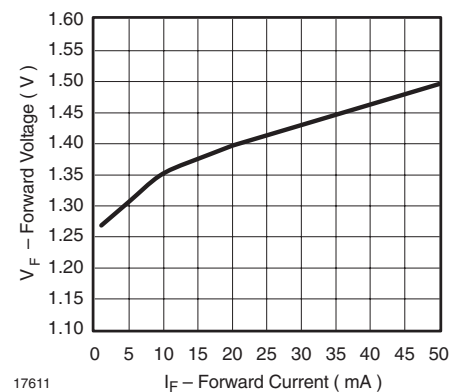


Figure 7. Forward Voltage vs. Forward Current

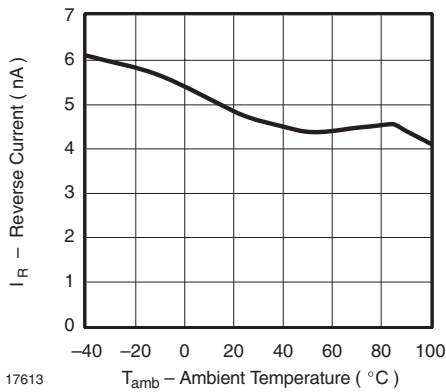


Figure 8. Reverse Current vs. Ambient Temperature

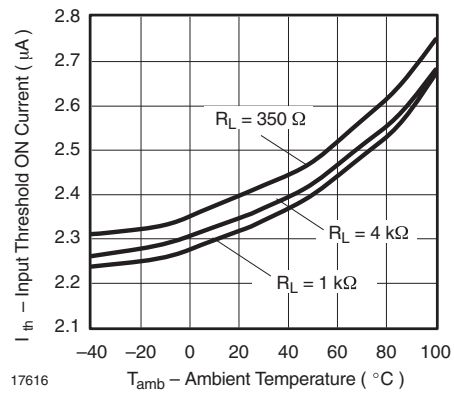


Figure 11. Input Threshold ON Current vs. Ambient Temperature

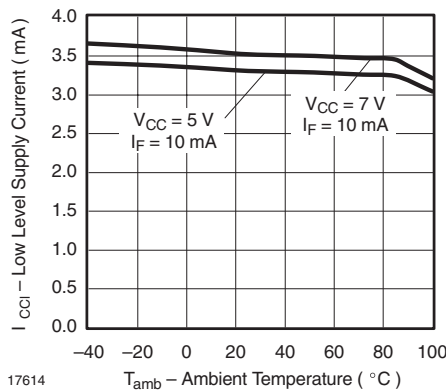


Figure 9. Low Level Supply Current vs. Ambient Temperature

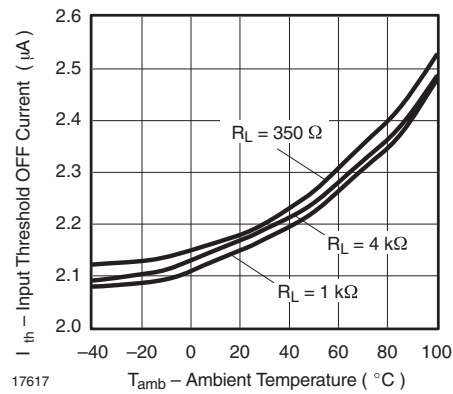


Figure 12. Input Threshold OFF Current vs. Ambient Temperature

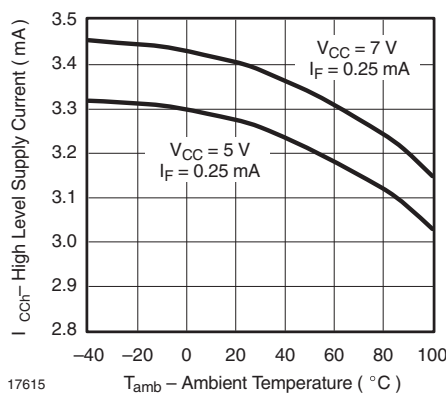


Figure 10. High Level Supply Current vs. Ambient Temperature

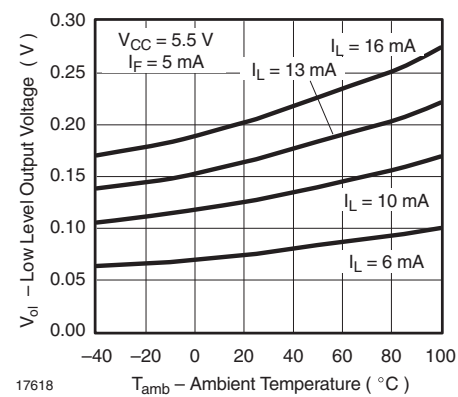


Figure 13. Low Level Output Voltage vs. Ambient Temperature

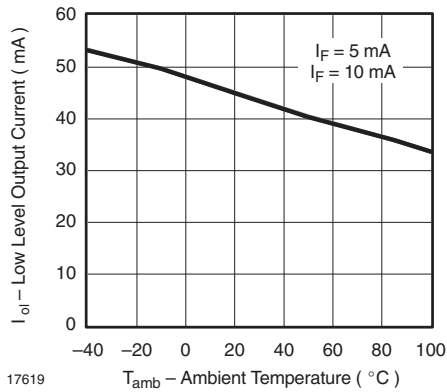


Figure 14. Low Level Output Current vs. Ambient Temperature

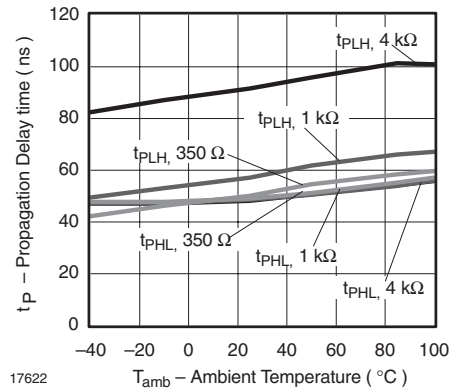


Figure 17. Propagation Delay vs. Ambient Temperature

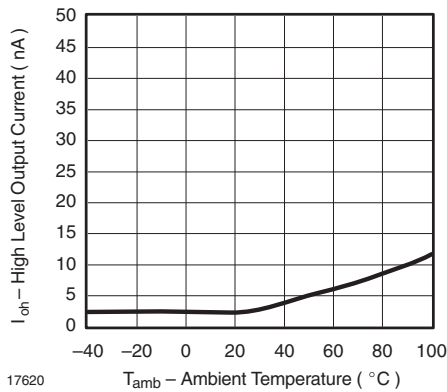


Figure 15. High Level Output Current vs. Ambient Temperature

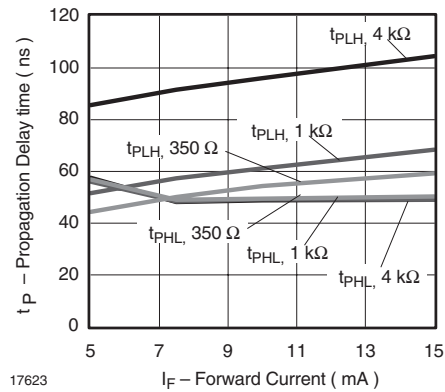


Figure 18. Propagation Delay vs. Forward Current

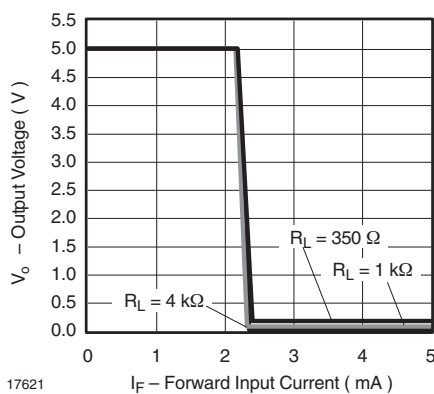


Figure 16. Output Voltage vs. Forward Input Current

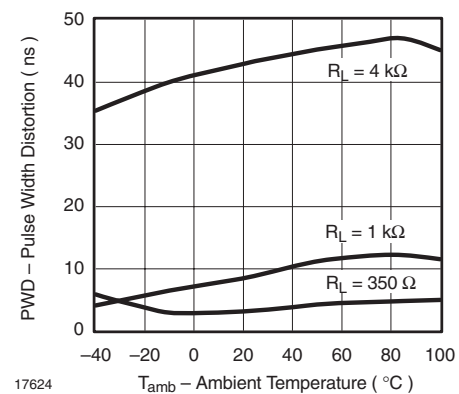


Figure 19. Pulse Width Distortion vs. Ambient Temperature

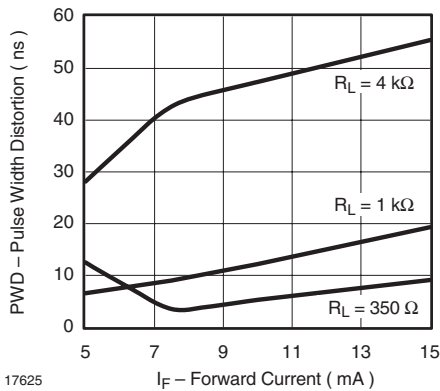


Figure 20. Pulse Width Distortion vs. Forward Current

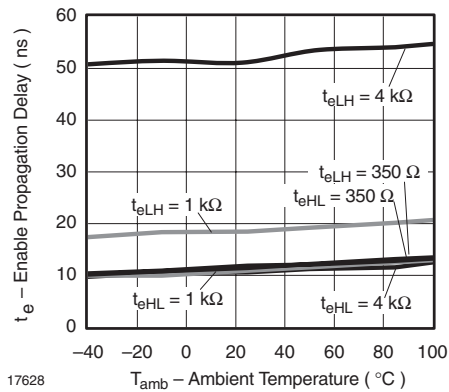


Figure 23. Enable Propagation Delay vs. Ambient Temperature

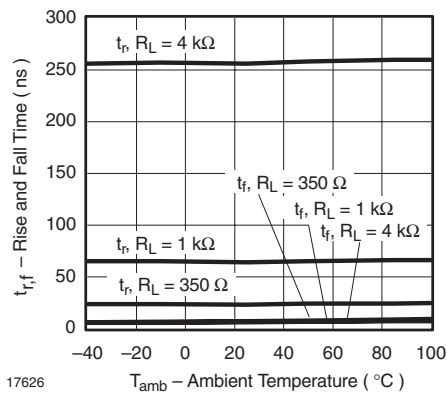


Figure 21. Rise and Fall Time vs. Ambient Temperature

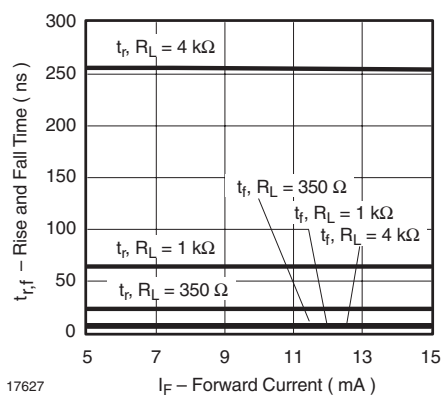
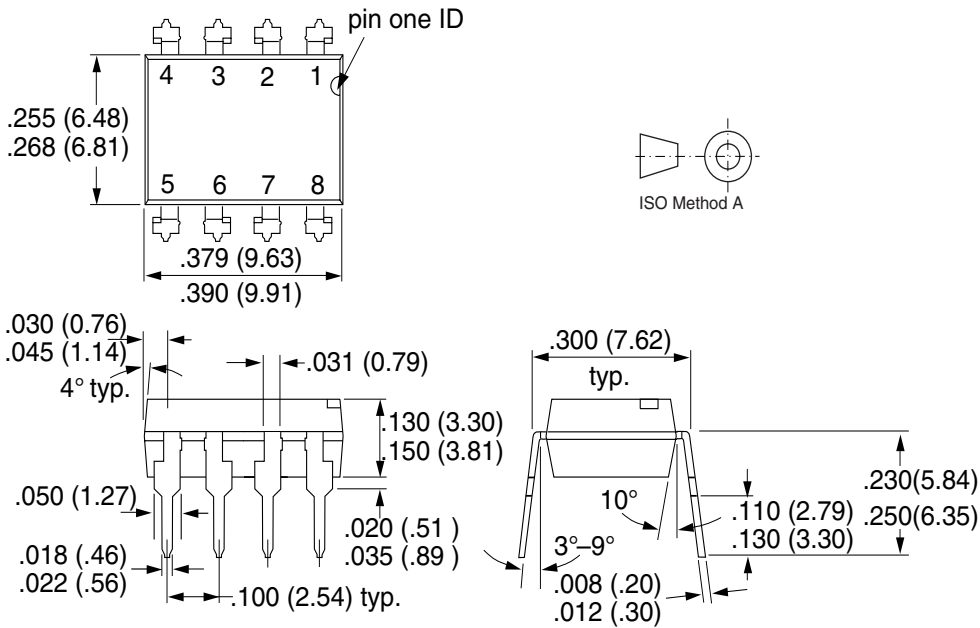


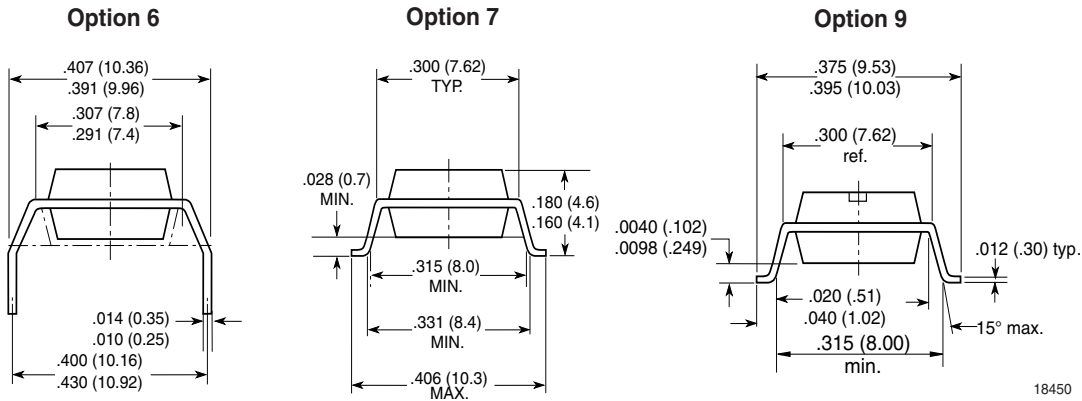
Figure 22. Rise and Fall Time vs. Forward Current



Package Dimensions in Inches (mm)



i178006



18450

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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Vishay Semiconductors
